

FS5AS-06

High-Speed Switching Use
Nch Power MOS FET

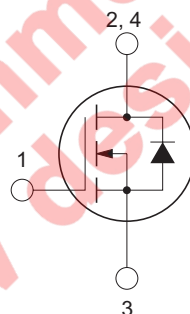
REJ03G1404-0200
(Previous: MEJ02G0087-0101)
Rev.2.00
Aug 07, 2006

Features

- Drive voltage : 10 V
- V_{DSS} : 60 V
- $r_{DS(ON) (max)}$: 0.16 Ω
- I_D : 5 A
- Integrated Fast Recovery Diode (TYP.) : 45 ns

Outline

RENESAS Package code: PRSS0004ZA-A
(Package name: MP-3A)



1. Gate
2. Drain
3. Source
4. Drain

Applications

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

Maximum Ratings

($T_c = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V_{DSS}	60	V	$V_{GS} = 0 \text{ V}$
Gate-source voltage	V_{GSS}	± 20	V	$V_{DS} = 0 \text{ V}$
Drain current	I_D	5	A	
Drain current (Pulsed)	I_{DM}	20	A	
Avalanche drain current (Pulsed)	I_{DA}	5	A	$L = 100 \mu\text{H}$
Source current	I_S	5	A	
Source current (Pulsed)	I_{SM}	20	A	
Maximum power dissipation	P_D	20	W	
Channel temperature	T_{ch}	-55 to $+150$	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to $+150$	$^\circ\text{C}$	
Mass	—	0.32	g	Typical value

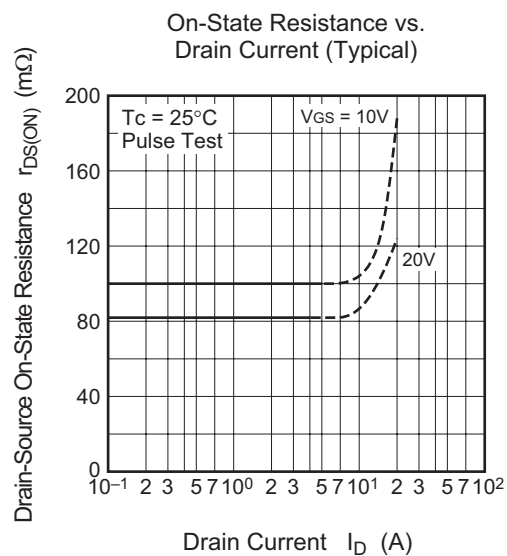
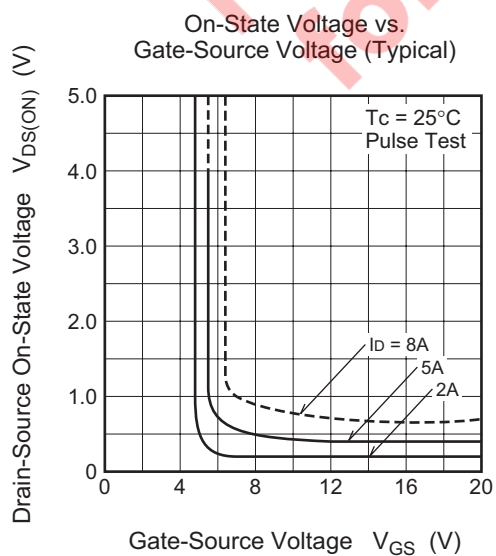
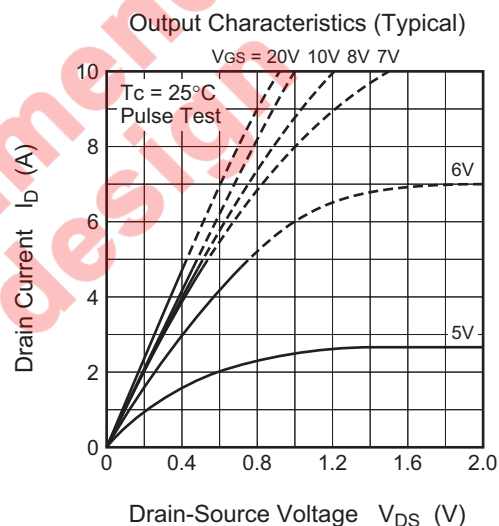
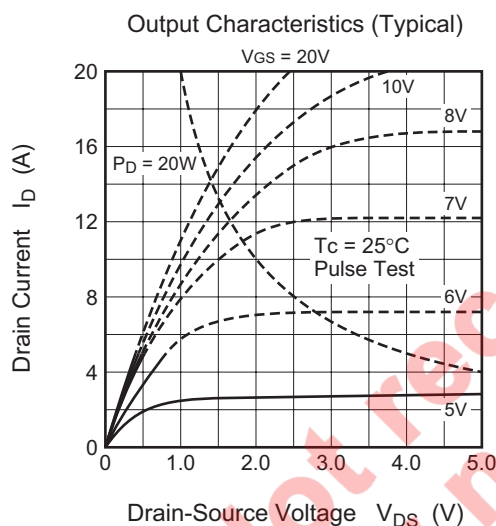
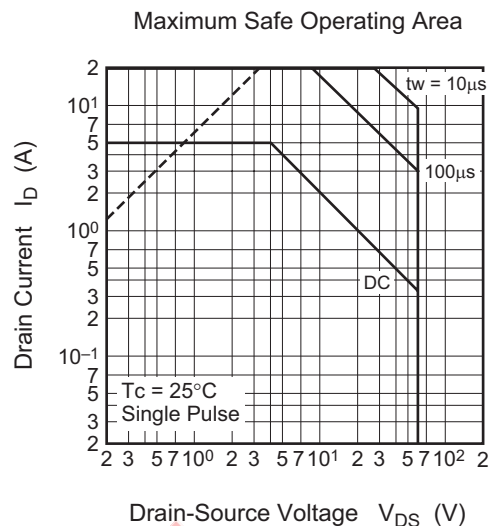
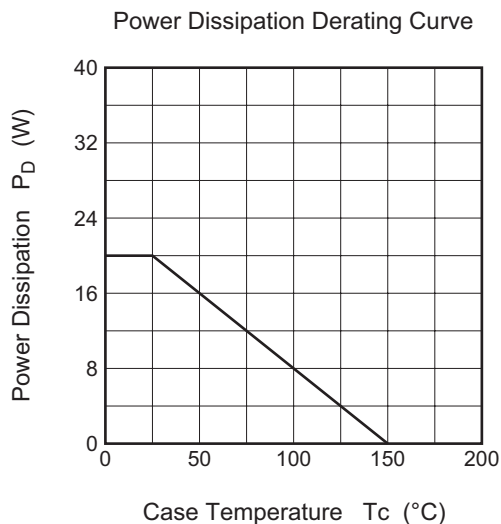
Electrical Characteristics

(T_{ch} = 25°C)

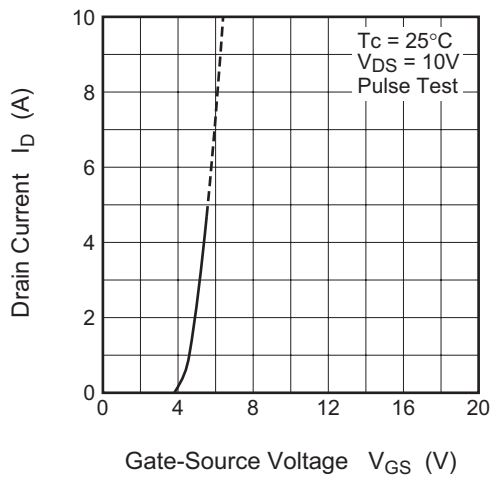
Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 1 \text{ mA}$, $V_{GS} = 0 \text{ V}$
Gate-source leakage current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$
Drain-source leakage current	I_{DSS}	—	—	0.1	mA	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	0.12	0.16	Ω	$I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}$
Drain-source on-state voltage	$V_{DS(ON)}$	—	0.24	0.32	V	$I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}$
Forward transfer admittance	$ y_{fs} $	—	4.0	—	S	$I_D = 2 \text{ A}$, $V_{DS} = 5 \text{ V}$
Input capacitance	C_{iss}	—	280	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	120	—	pF	
Reverse transfer capacitance	C_{rss}	—	35	—	pF	
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$V_{DD} = 30 \text{ V}$, $I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_{GEN} = R_{GS} = 50 \Omega$
Rise time	t_r	—	8	—	ns	
Turn-off delay time	$t_{d(off)}$	—	18	—	ns	
Fall time	t_f	—	9	—	ns	
Source-drain voltage	V_{SD}	—	1.0	1.5	V	$I_S = 2 \text{ A}$, $V_{GS} = 0 \text{ V}$
Thermal resistance	$R_{th(ch-c)}$	—	—	6.25	$^{\circ}\text{C/W}$	Channel to case
Reverse recovery time	t_{rr}	—	45	—	ns	$I_S = 5 \text{ A}$, $dI_S/dt = -100 \text{ A}/\mu\text{s}$

Not recommended
for new design

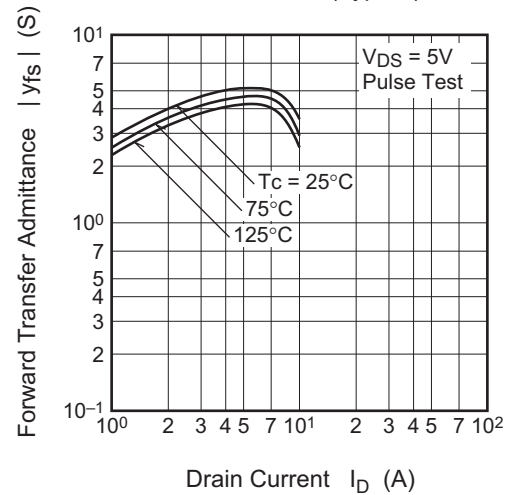
Performance Curves



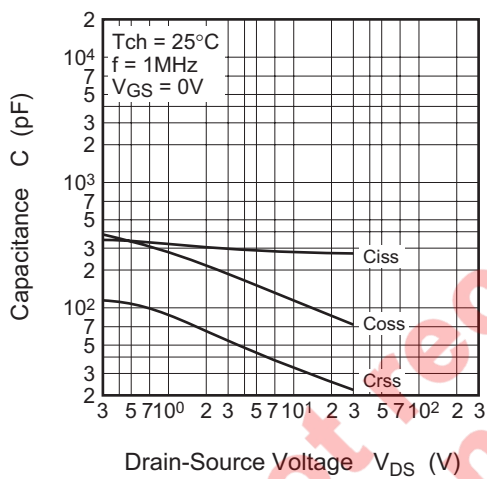
Transfer Characteristics (Typical)



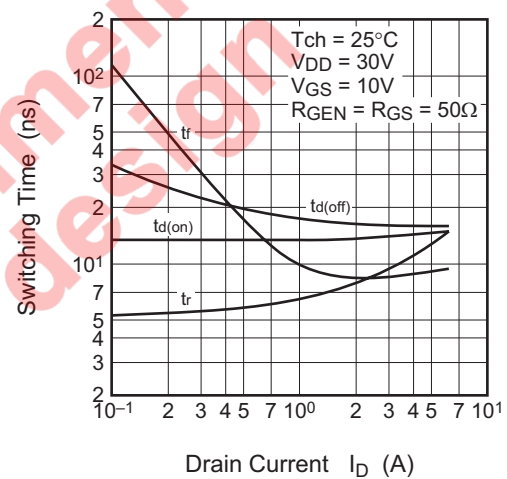
Forward Transfer Admittance vs. Drain Current (Typical)



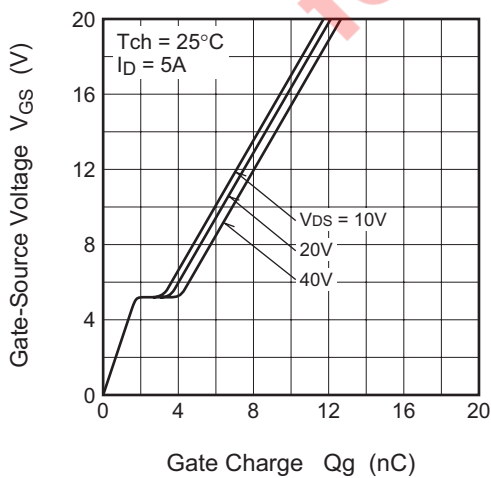
Capacitance vs. Drain-Source Voltage (Typical)



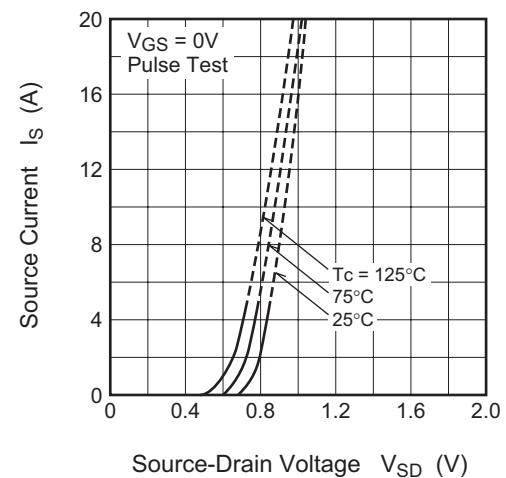
Switching Characteristics (Typical)

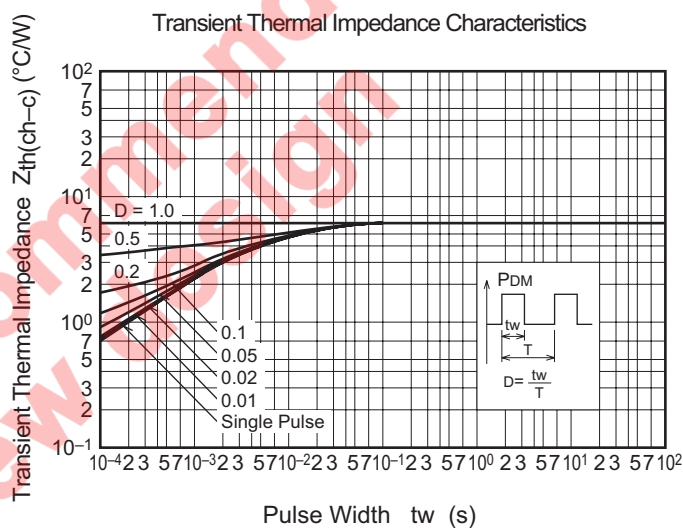
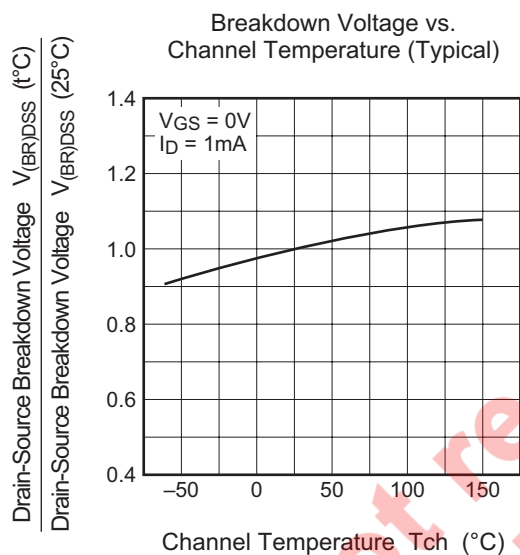
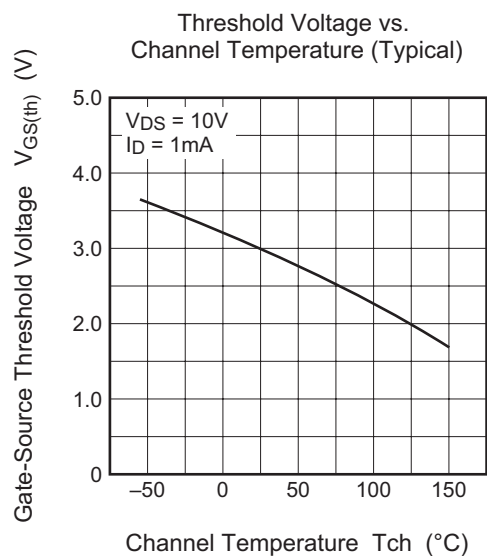
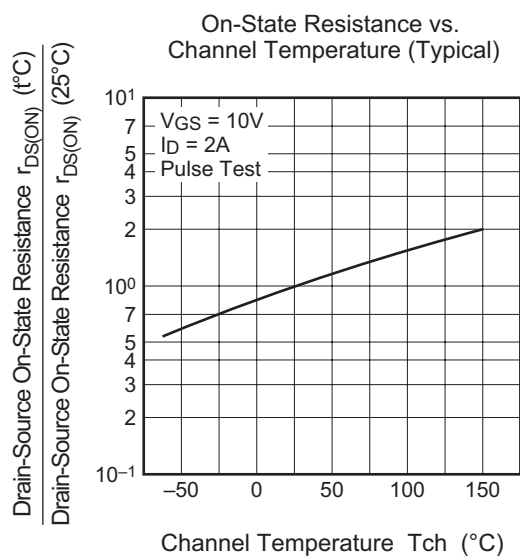


Gate-Source Voltage vs. Gate Charge (Typical)

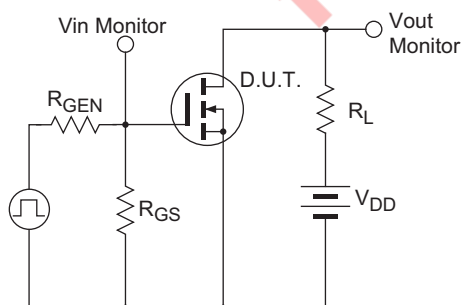


Source-Drain Diode Forward Characteristics (Typical)

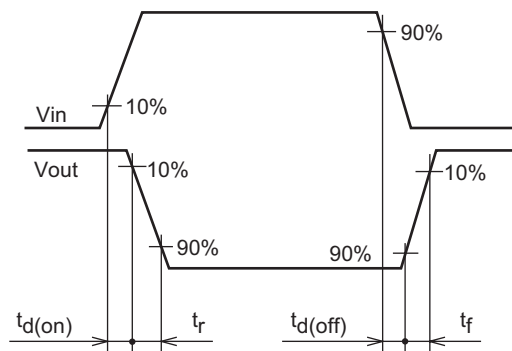




Switching Time Measurement Circuit



Switching Waveform



Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]	Unit: mm
MP-3A	SC-63	PRSS0004ZA-A	—	0.32g	

The drawing shows the following dimensions (all in mm):

- Top View:** Overall width 6.6, inner width 5.3 ± 0.2 , lead width 0.76 ± 0.2 , lead pitch 2.3 ± 0.2 , and lead width 0.76 .
- Side View:** Overall height 10.4Max , mounting tab height 1 ± 0.2 , mounting tab width 2.3 , and mounting tab thickness 0.5 ± 0.2 .
- Bottom View:** Overall width 2.3 ± 0.2 , lead width 0.76 , and lead pitch 2.3 ± 0.2 .

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FS5AS-06-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FS5AS-06

Note : Please confirm the specification about the shipping in detail.

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Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.

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Renesas Technology Hong Kong Ltd.

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Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.

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Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

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Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510